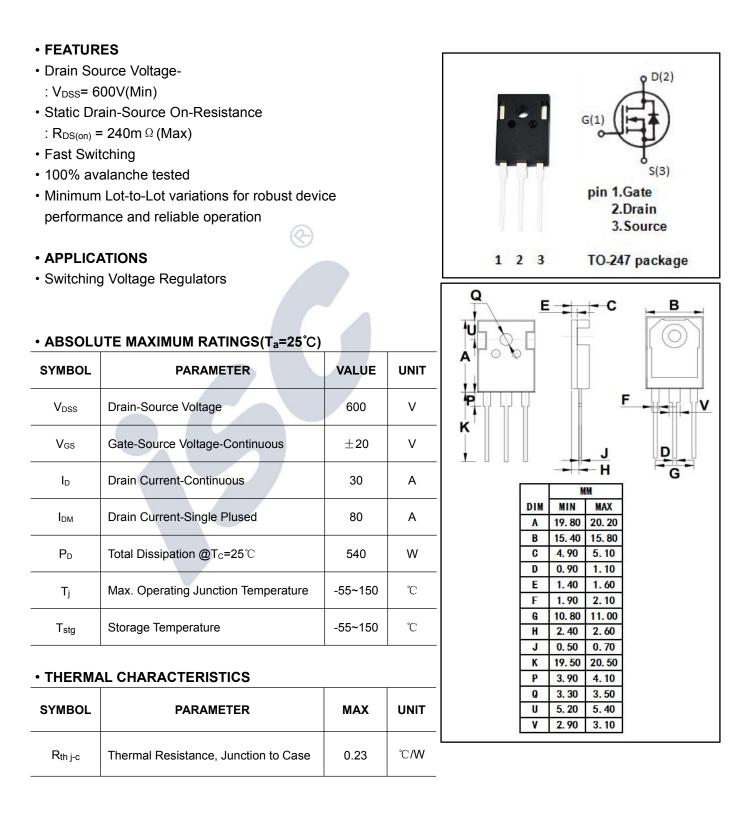


INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXTH30N60L2



isc website: <u>www.iscsemi.com</u>



isc N-Channel MOSFET Transistor

IXTH30N60L2

• ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D =1mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V_{DS} = V_{GS} ; I _D =250uA	2.5		4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 15A			240	$\mathbf{m}\Omega$
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V;V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V; V _{GS} = 0 V _{DS} =600V; V _{GS} = 0;TJ=125℃			50 300	μA
V _{SD}	Diode Forward On-voltage	IF= 30A ;V _{GS} = 0			1.5	V

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